Supporting Information

Quantum Spin Hall Insulators in Strain-modified Arsenene

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Figure S1  Strain dependent of functional energy gaps $E_g (F)$ and band gaps at G point $E_g (G)$.

Figure S2  Enlarged band structures around Fermi level for arsenene with different strain. Green dashed lines represents Fermi level at 0 eV.
Figure S3 Band structure of arsenene under strain of 18.4%, calculated by HSE06 method with SOC effect.